



FIG. 3. Energy band structure of ZB (shaded) SiGe, and rhombohedral (RH) SiGe as functions of the lattice constant a (Å) for epitaxially grown ZB and RH SiGe on $a_{\text{Si}} = 3.57$ Å $1 \times 1 \times 1$ substrate. The energy scale was adjusted such that the minimum of the curve gives the enthalpy of formation. ΔE_{ss} denotes the substrate strain. The shaded area denotes the negative enthalpy of formation of ZB-SiGe. Energy value of 0 eV was used.